

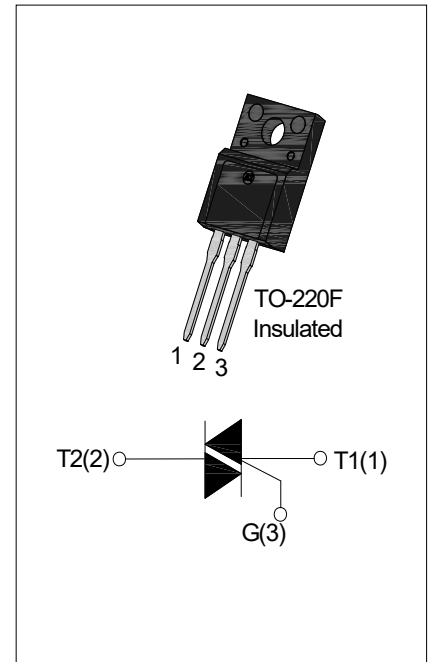


## JST08F-800SW 8A TRIACs

Rev.1

### DESCRIPTION:

With high ability to withstand the shock loading of large current, JST08F-800SW triacs provide high dv/dt rate with strong resistance to electromagnetic interface. With high commutation performances, especially recommended for use on inductive load. From all three terminals to external heatsink, JST08F-800SW provides a rated insulation voltage of 2000 V<sub>RMS</sub>, complying with UL standards (File ref: E252906). Package TO-220F is RoHS compliant.(2011/65/EU)



### MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	8	A
$V_{DRM}/V_{RRM}$	800	V

### ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		$T_{stg}$	-40 - 150	°C
Operating junction temperature range		$T_j$	-40 - 125	°C
Repetitive peak off-state voltage ( $T_j=25^\circ\text{C}$ )		$V_{DRM}$	800	V
Repetitive peak reverse voltage ( $T_j=25^\circ\text{C}$ )		$V_{RRM}$	800	V
RMS on-state current	TO-220F(Ins) ( $T_c=95^\circ\text{C}$ )	$I_{T(RMS)}$	8	A
Non repetitive surge peak on-state current (full cycle, F=50Hz)		$I_{TSM}$	80	A
$I^2t$ value for fusing ( $t_p=10\text{ms}$ )		$I^2t$	32	A <sup>2</sup> s
Critical rate of rise of on-state current ( $I_G=2 \times I_{GT}$ )		$di/dt$	50	A/ $\mu\text{s}$
Peak gate current		$I_{GM}$	4	A
Average gate power dissipation		$P_{G(AV)}$	1	W
Peak gate power		$P_{GM}$	5	W

**ELECTRICAL CHARACTERISTICS** ( $T_j=25^\circ\text{C}$  unless otherwise specified)

Symbol	Test Condition	Quadrant		Value	Unit
$I_{GT}$	$V_D=12\text{V } R_L=33\Omega$	I - II -III	MAX	10	mA
$V_{GT}$		I - II -III	MAX	1.5	V
$V_{GD}$	$V_D=V_{DRM} T_j=125^\circ\text{C}$ $R_L=3.3\text{K}\Omega$	I - II -III	MIN	0.2	V
$I_L$	$I_G=1.2I_{GT}$	I -III	MAX	25	mA
		II		35	
$I_H$	$I_{TM}=100\text{mA}$		MAX	20	mA
dv/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^\circ\text{C}$		MIN	200	V/ $\mu\text{s}$

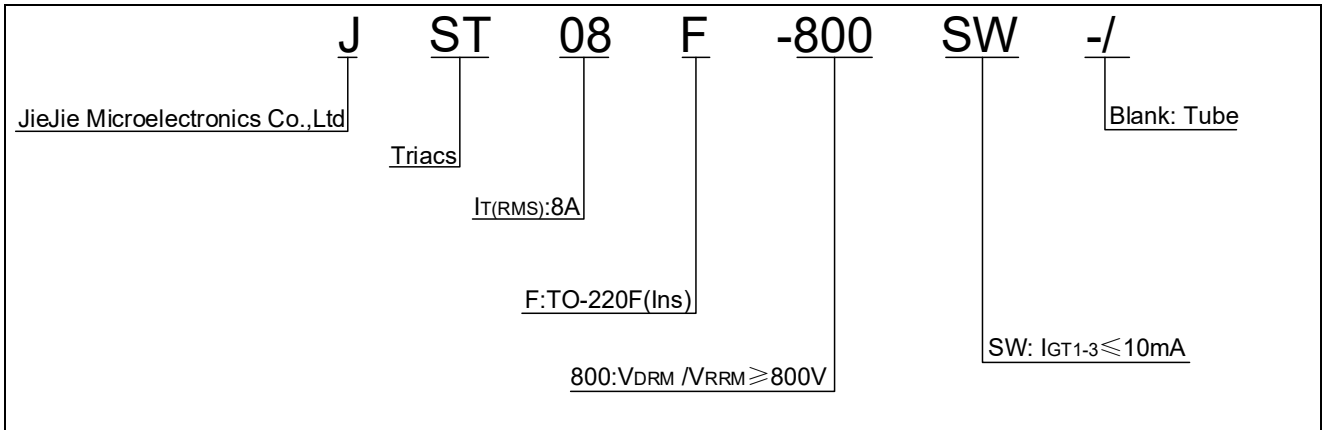
**STATIC CHARACTERISTICS**

Symbol	Parameter		Value(MAX)	Unit
$V_{TM}$	$I_{TM}=11\text{A } t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.5	V
$V_{TO}$	Threshold voltage	$T_j=125^\circ\text{C}$	0.95	V
$R_d$	Dynamic resistance	$T_j=125^\circ\text{C}$	40	m $\Omega$
$I_{DRM}$	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	5	$\mu\text{A}$
$I_{RRM}$		$T_j=125^\circ\text{C}$	1	mA

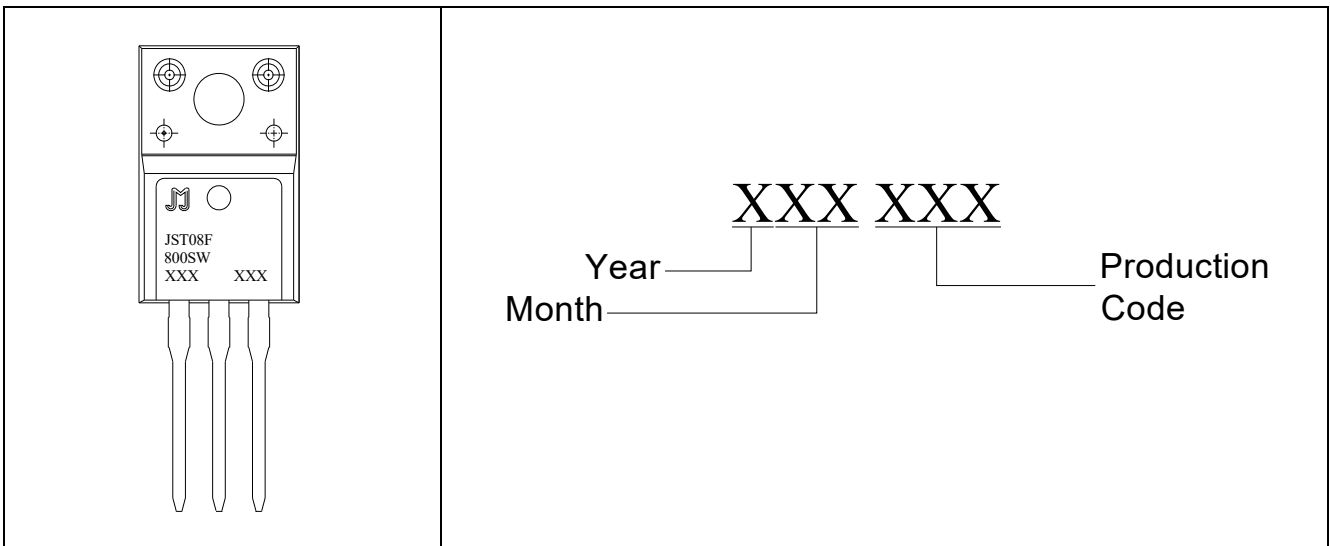
**THERMAL RESISTANCES**

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-220F(Ins)	2.9	$^\circ\text{C}/\text{W}$

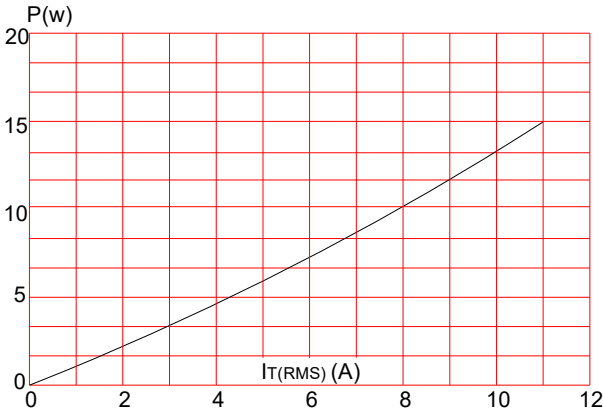
**ORDERING INFORMATION**



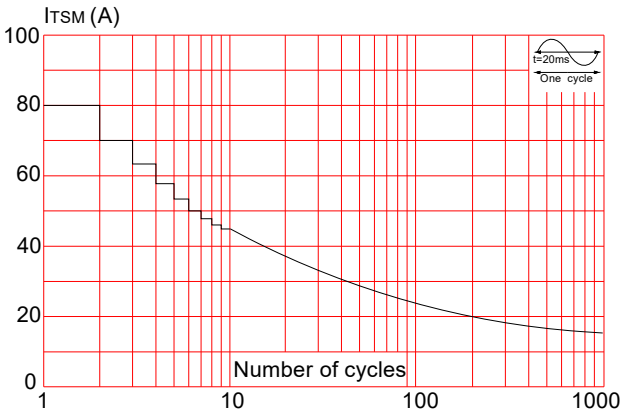
**MARKING**



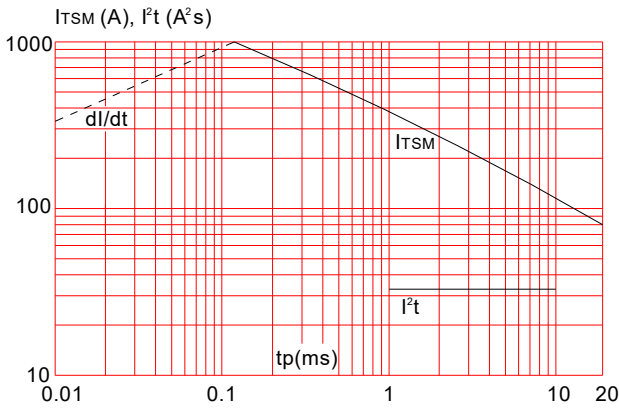
**FIG.1:** Maximum power dissipation versus RMS on-state current



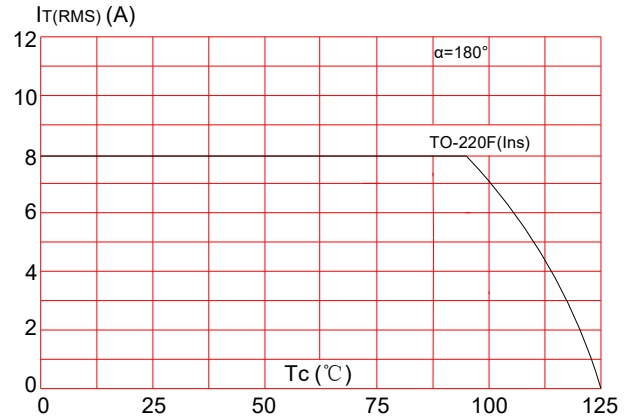
**FIG.3:** Surge peak on-state current versus number of cycles



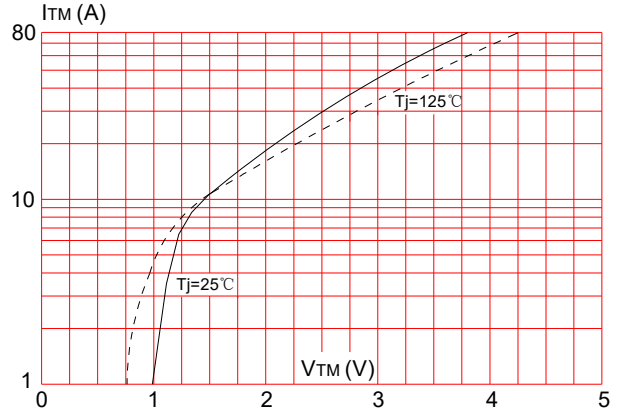
**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 20\text{ms}$ , and corresponding value of  $I^2t$  ( $di/dt < 50\text{A}/\mu\text{s}$ )



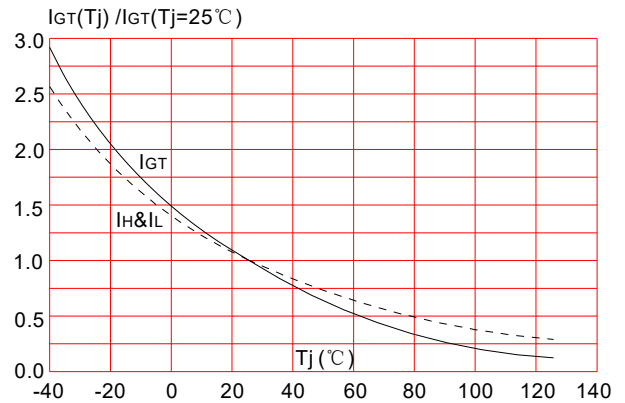
**FIG.2:** RMS on-state current versus case temperature



**FIG.4:** On-state characteristics (maximum values)



**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature



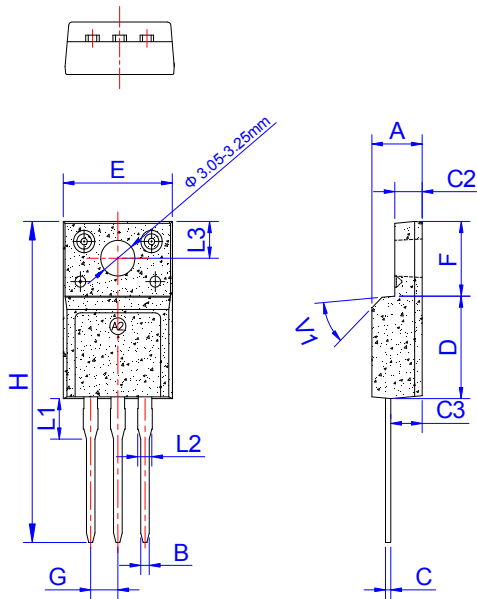
**ORDERING INFORMATION**

Order code	Voltage $V_{DRM}/V_{RRM}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		I - II -III			
JST08F-800SW	800	10	TO-220F(Ins)	50	Tube

**Document Revision History**

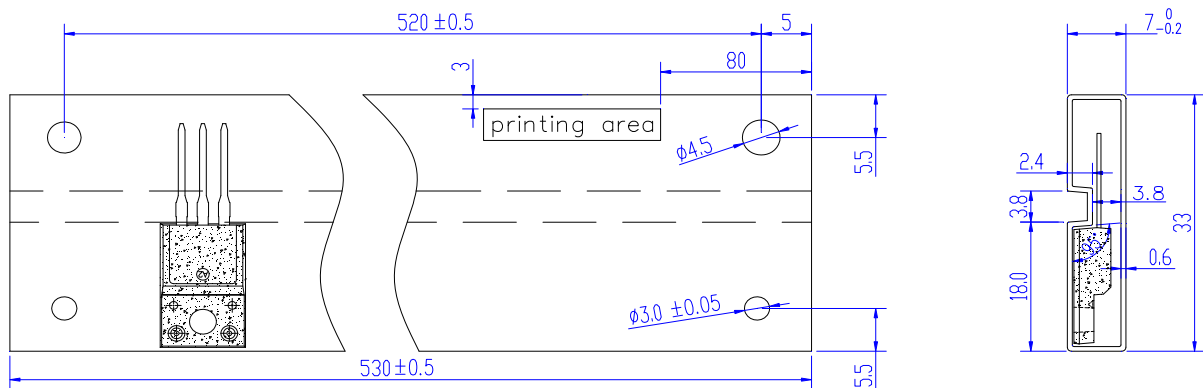
Date	Revision	Changes
Mar 18, 2022	1	Last update

**PACKAGE MECHANICAL DATA**



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.50		4.90	0.177		0.193
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.47		0.65	0.019		0.026
C2	2.45		2.75	0.096		0.108
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.80		10.4	0.386		0.410
F	6.40		6.80	0.252		0.268
G	2.40		2.70	0.094		0.106
H	28.0		29.8	1.102		1.173
L1		3.63			0.143	
L2		1.14	1.70		0.045	0.067
L3		3.30			0.130	
V1		45°			45°	


**DELIVERY MODE**



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-220F	TUBE	50	1,000	5,000



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